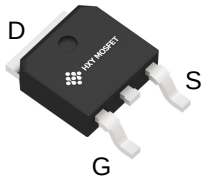
HSTD35NF06LT4

N-Channel Enhancement Mode MOSFET

Description

The HSTD35NF06LT4 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

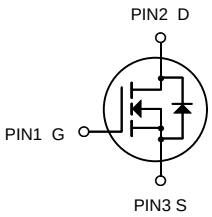


TO-252-2L (DPAK)

General Features

V_{DS} = 60V I_D =50 A

$R_{DS(ON)}$ < 17mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HSTD35NF06LT4	TO-252-2L(DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	50	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	38	A
I_{DM}	Pulsed Drain Current[2]	180	A
EAS	Single Pulse Avalanche Energy[3]	280	mJ
I_{AS}	Avalanche Current	28	A
P_D@T_C=25℃	Total Power Dissipation[4]	87.7	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	62	℃/W

Electrical Characteristics (T_C =25℃unless otherw ise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.5	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=30A	-	13	17	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=30A	30	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	2498	-	PF
Output Capacitance	C_{oss}		-	185	-	PF
Reverse Transfer Capacitance	C_{rss}		-	80	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=2A,R_L=1Ω V_{GS}=10V,R_{GEN}=3Ω	-	12	-	nS
Turn-on Rise Time	t_r		-	5.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	t_f		-	27	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=30A, V_{GS}=10V	-	36	-	nC
Gate-Source Charge	Q_{gs}		-	9.9	-	nC
Gate-Drain Charge	Q_{gd}		-	6.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=30A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	58	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF =30A di/dt = 100A/μs (Note3)	-	35		nS
Reverse Recovery Charge	Qrr		-	47		nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: Tj=25℃,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25Ω

Typical Electrical and Thermal Characteristics (Curves)

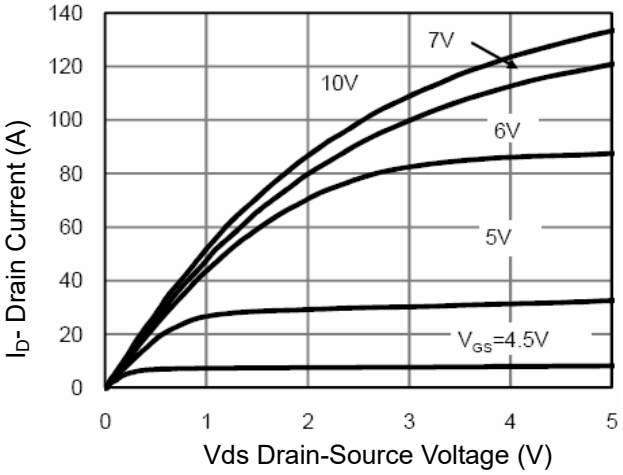


Figure 1 Output Characteristics

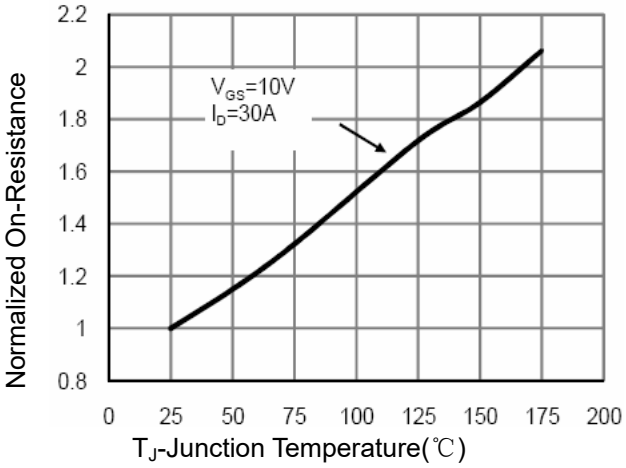


Figure 4 Rdson-JunctionTemperature

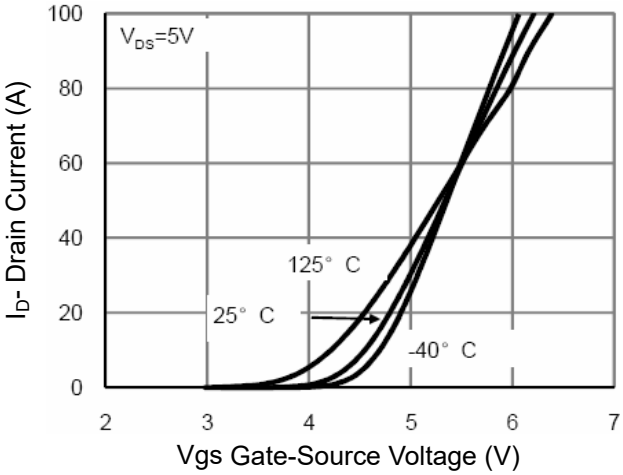


Figure 2 Transfer Characteristics

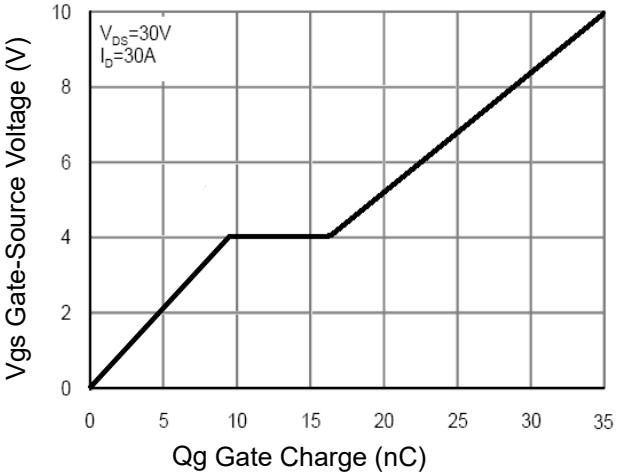


Figure 5 Gate Charge

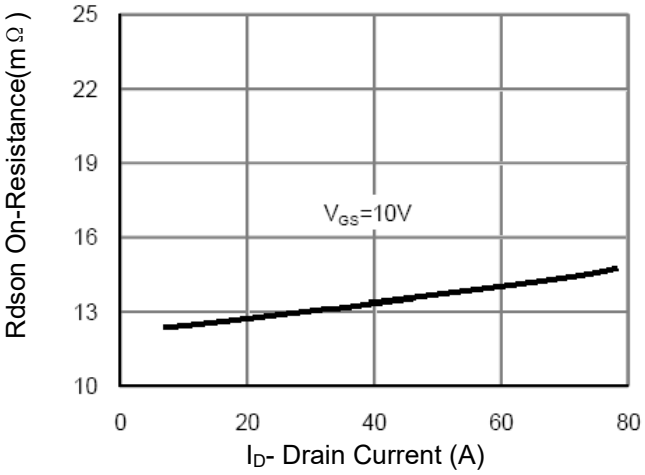


Figure 3 Rdson- Drain Current

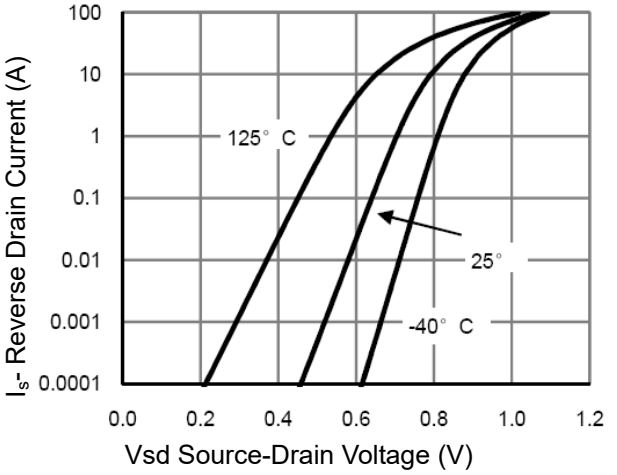


Figure 6 Source- Drain Diode Forward

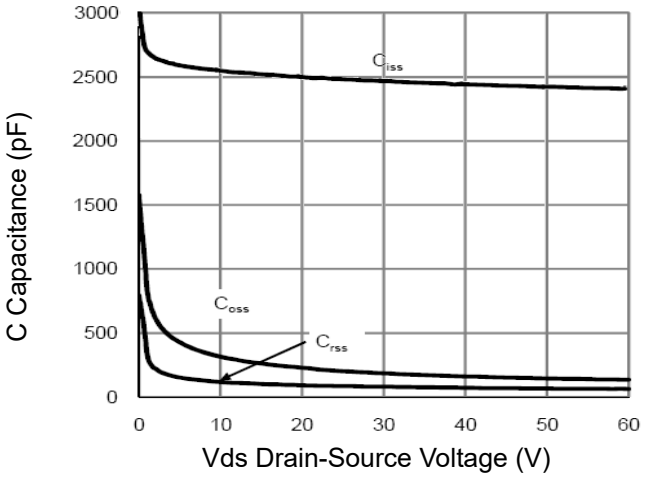


Figure 7 Capacitance vs Vds

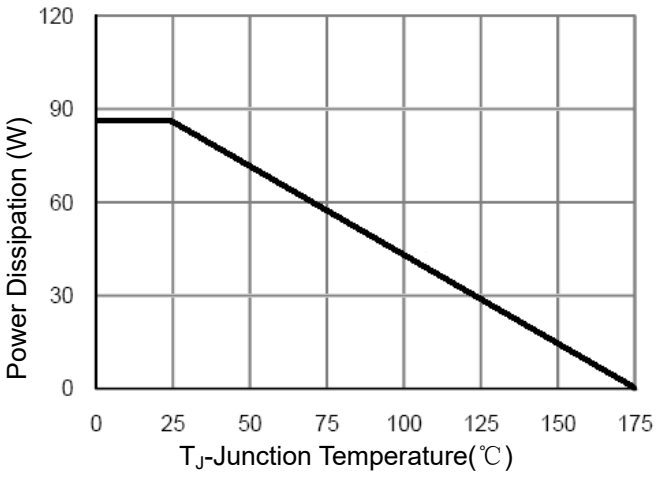


Figure 9 Power De-rating

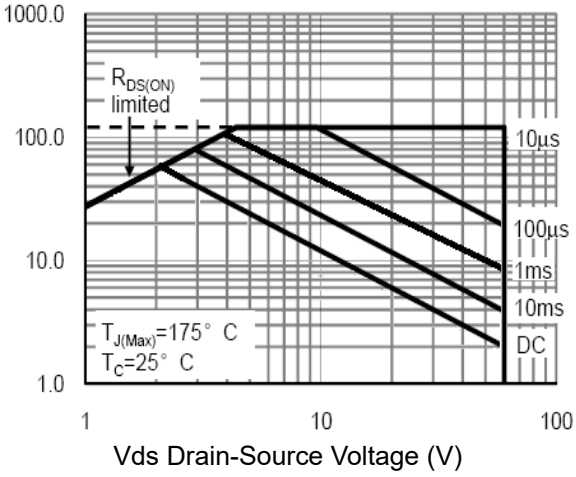


Figure 8 Safe Operation Area

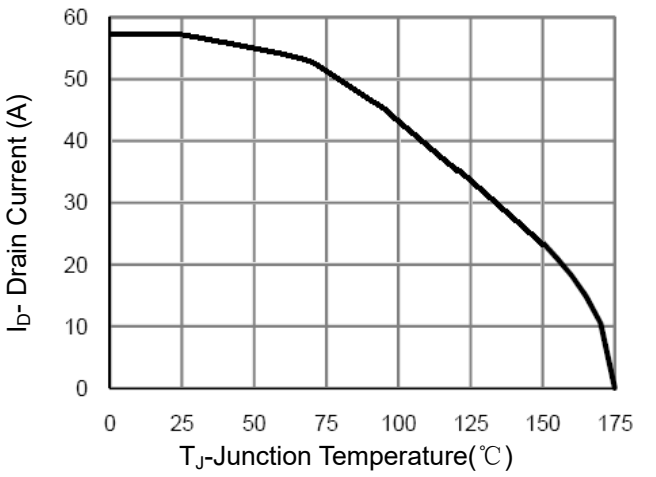
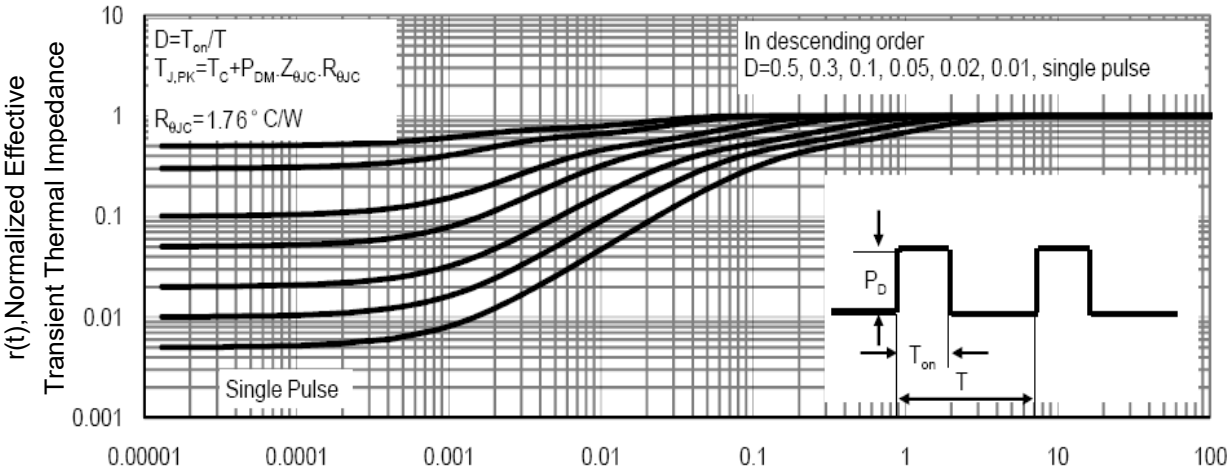
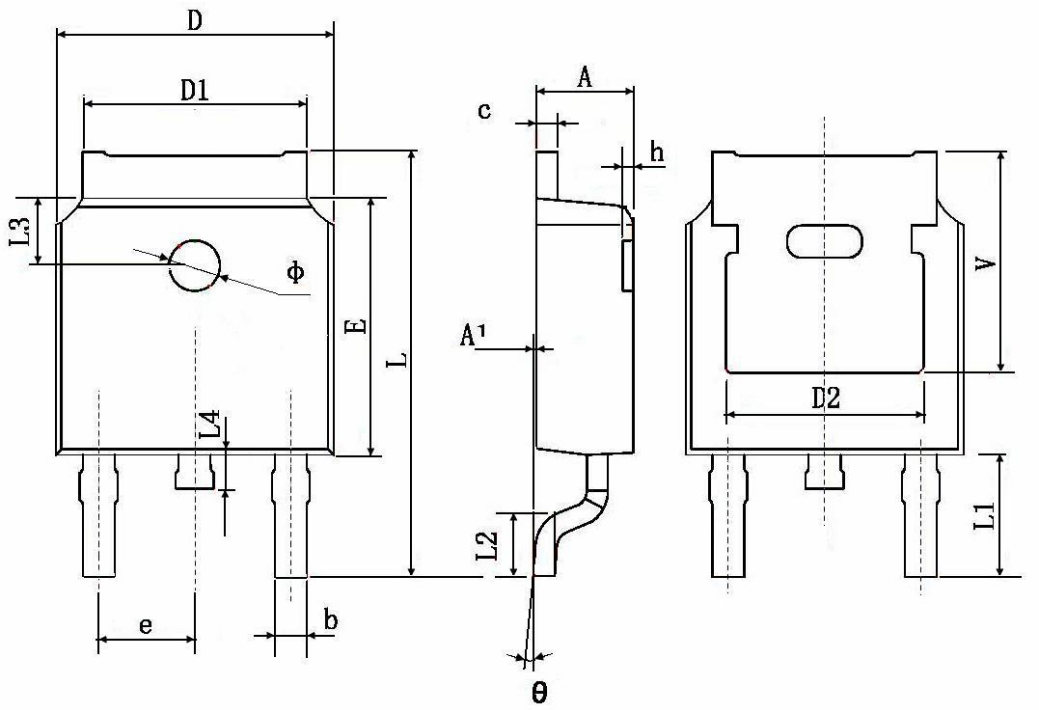


Figure 10 ID Current- JunctionTemperature



TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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